

**ABSTRACT**

The present invention provides a method of testing silicon carbide (SiC) semiconductor device (103) configured to perform parallel testing, which provides faster testing throughput. The method involves utilizing a primary rotary transfer mechanism (105) and at least one secondary rotary transfer mechanism, whereby one primary rotary transfer mechanism (105) may transfer semiconductor devices (103) to a single or a plurality of secondary rotary transfer mechanisms. Once the semiconductor devices are transferred from said primary rotary transfer mechanism (105) to said secondary rotary transfer mechanism, said secondary rotary transfer mechanism is then configured to transfer said semiconductor devices (103) to at least one pre-test station, at least one test station and at least one post-test station to perform the necessary electrical conductivity and functionality test on said semiconductor devices (103). The present invention also provides the system for performing said testing on said SiC semiconductor devices (103).

(Fig. 17)